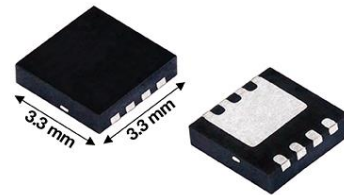




Best in Class SiSS52DN 30 V N-Channel MOSFET Delivers High Power Density and Efficiency for Isolated and Non-Isolated Topologies, With $R_{DS(ON)}$ Down to 0.95 m Ω and Enhanced FOM and R_g Parameters in PowerPAK[®] 1212-8S Package

Product Benefits:

- Best in class on-resistance: 0.95 m Ω at 10 V
- One of the lowest FOMs on the market: 29.8 m Ω *nC
- Offered in the 3.3 mm by 3.3 mm thermally enhanced PowerPAK 1212-8S package
- 100 % R_G - and UIS-tested, RoHS-compliant, and halogen-free



Market Applications:

- Low side switching for synchronous rectification, synchronous buck converters, DC/DC converters, switch tank topologies, OR-ring FETs, and load switches for power supplies in servers and telecom and RF equipment

The News:

Vishay Intertechnology introduces a versatile new 30 V n-channel TrenchFET[®] Gen V power MOSFET that delivers increased power density and efficiency for both isolated and non-isolated topologies.

- Saves energy in power conversion applications
- By delivering high performance in isolated and non-isolated topologies, the MOSFET simplifies part selection for designers working with both



The Key Specifications:

- Package: PowerPAK 1212-8S
- Drain-source voltage: 30 V
- Maximum on-resistance:
 - At 10 V: 1.2 m Ω
 - At 4.5 V: 1.9 m Ω
- Typical on-resistance:
 - At 10 V: 0.95 m Ω
 - At 4.5 V: 1.5 m Ω
- Maximum gate charge:
 - At 10 V: 65 nC
 - At 4.5 V: 30 nC
- Typical gate charge:
 - At 10 V: 43.2 nC
 - At 4.5 V: 19.9 nC

Availability:

Samples and production quantities of the SiSS52DN are available now, with lead times of 12 weeks.

To access the product datasheet on the Vishay Website, go to <http://www.vishay.com/ppg?79977> (SiSS52DN)

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